## High Gain RF Amplifier, 75 Ω, 50-1200 MHz



### **Applications**

- Distribution Amplifiers
- Multi Dwelling Units
- Drop Amplifiers
- Single Ended Gain Blocks



#### **Product Features**

50-1200 MHz Bandwidth

High Gain: 18.5 dB+38 dBm typical OIP3

• 2.5 dB typical NF

• Low Distortion : CSO -70dBc, CTB -88dBc tested at 10dBmV/ch at input, 80 ch NTSC

• pHEMT Device Technology

SOT-89 Package

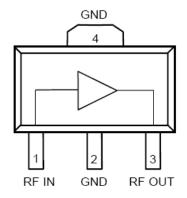
• Single +8V Supply

## **General Description**

The TAT7427B is a high gain 75  $\Omega$  RF Amplifier designed for CATV applications from 50 to 1000 MHz (with operation up to 1.25GHz). The balance of low noise and distortion provides an ideal solution for drop and distribution amplifiers. It is particularly well suited for new home networks requiring higher gain for a large number of splits.

The TAT7427B is fabricated using 6-inch GaAs pHEMT technology to optimize performance and cost. It provides excellent gain and return loss consistency inherent to the pHEMT process.

## **Functional Block Diagram**



# **Pin Configuration**

Pin #	Symbol
1	RF_Input
2, 4	Ground
3	RF_Output / V <sub>dd</sub>

## **Ordering Information**

Part No.	Description
TAT7427B-T1	High Gain 75 Ω RF Amplifier (Lead free / RoHS compliant SOT-89 Pkg)
TAT7427B-T1-EB	Drop Amplifier Evaluation Board

Standard T/R size = 1000 pieces on a 7" reel.

Data Sheet: Rev A 08-30-10 © 2010 TriQuint Semiconductor, Inc.

- 1 of 7 - Disclaimer: Subject to change without notice

Connecting the Digital World to the Global Network®

# High Gain RF Amplifier, 75 Ω, 50-1200 MHz



## **Specifications**

#### **Absolute Maximum Ratings**

# **Recommended Operating Conditions**

Parameter	Rating	Parameter	Min	Тур	Max	Units
Storage Temperature	-55 to 150 °C	$ m V_{dd}$		8		V
Thermal Resistance	TBD °C/W	Operating Case Temperature	-20		85	°C
		$T_i$ (For $> 10^6$ MTTF)			150	°C

Operation of this device outside the parameter ranges given above may cause permanent damage.

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

#### **Electrical Specifications**

Test conditions: Case Temperature 25°C

Parameter	Conditions	Min	Typical	Max	Units
Operational Frequency Range		50		1002	MHz
Gain			18.5		dB
Gain Flatness			±0.3		dB
Noise Figure			2.5		dB
Input Return Loss			23		dB
Output Return Loss			20		dB
CSO	10 dBmV/ch at input, 80 ch NTSC flat		-70		dBc
СТВ	10 dBmV/ch at input, 80 ch NTSC flat		-88		dBc
Output IP2	See Note 1.		61		dBm
Output IP3	See Note 1.		38		dBm
Supply Voltage, Vcc			+8		V
Device Voltage			+6		V
Supply Current, Idd	See Note 2.		145	175	mA

#### Notes:

1. OIP3 and OIP2 tested with two tones at 225 MHz and 325 MHz. Measured at 10 dBm/tone output power.

2. Voltage at the device is 6V.

Data Sheet: Rev A 08-30-10 © 2010 TriQuint Semiconductor, Inc.

- 2 of 7 - Disclaimer: Subject to change without notice

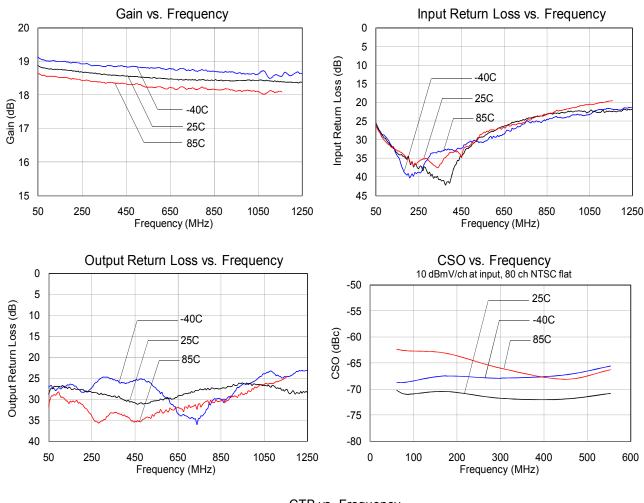
Connecting the Digital World to the Global Network®

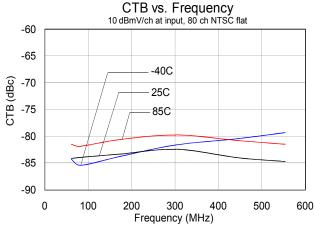
## High Gain RF Amplifier, 75 Ω, 50-1200 MHz



#### **Typical Performance Data**

Note: Temperature indicated in plots below is Case Temperature.





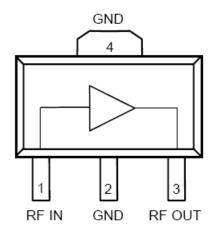
Data Sheet: Rev A 08-30-10 © 2010 TriQuint Semiconductor, Inc.

- 3 of 7 - Disclaimer: Subject to change without notice

Connecting the Digital World to the Global Network®



### **Pin Description**



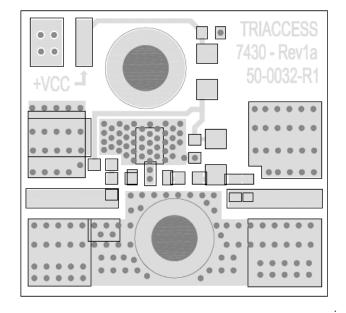
Pin	Symbol	Description
1	RF_IN	RF Input, DC voltage present, blocking capacitor required
2	GND	Ground
3	RF_OUT	RF Output, DC voltage present, blocking capacitor required
Backside Paddle	GND	Multiple vias should be employed to minimize inductance and thermal resistance

## **Applications Information**

## **PC Board Layout**

Core is 0.062", FR4,  $\epsilon_r$  = 4.7. Metal layers are 1-oz copper.

The pad pattern shown has been developed and tested for optimized assembly at TriQuint Semiconductor. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.



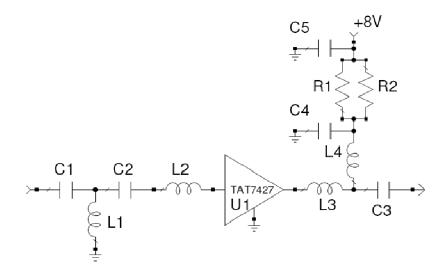
Data Sheet: Rev A 08-30-10 © 2010 TriQuint Semiconductor, Inc.

4 of 7 - Disclaimer: Subject to change without notice
 Connecting the Digital World to the Global Network<sup>®</sup>



# **Applications Information**

#### **PC Board Schematic**



#### **Bill of Material**

Reference Desg.	Value	Description	Manufacturer	Part Number
U1		RF Amplifier, 75 ohm , 50-1000MHz	TriQuint	TAT7427B
C1, C4, C5	0.01 uF	Cap, Chip, 0603, 10%, 50V, X7R	various	
_C2	680 pF	Cap, Chip, 0402, 50V, 5%, COG	various	
<u>C3</u>	120 pF	Cap, Chip, 0402, 50V, 5%, COG	various	
_L1	880 nH	Coil, Wire Wound, 1206, ±10%	various	
L2	3.9 nH	Inductor, Chip, 0603, 5%	various	
_L3	5.6 nH	Inductor, Chip, 0603, 5%	various	
_L4	500 nH	Coil, Wire Wound, 1206, ±10%	various	
R1, R2	16 Ω	Resistor, Chip, 1206, ±5%, 1/4W	various	

Data Sheet: Rev A 08-30-10 © 2010 TriQuint Semiconductor, Inc.

- 5 of 7 - Disclaimer: Subject to change without notice

Connecting the Digital World to the Global Network®



#### **Mechanical Information**

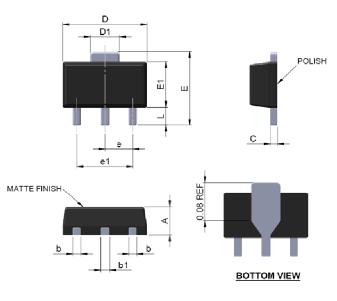
#### **Package Information and Dimensions**

This package is lead-free, RoHS-compliant, and green. The plating material on the pins is 100% matte tin. It is compatible with both lead-free (maximum 260 °C reflow temperature) and leaded (maximum 245 °C reflow temperature) soldering processes.

The TAT7427B will be marked with a "TAT7427B" designator and an 8 digit alphanumeric lot code (XXXXYYWW). The first 4 digits (XXXX) are the lot code. The last 4 digits (YYWW) are the date code consisting of the year and work week of assembly.

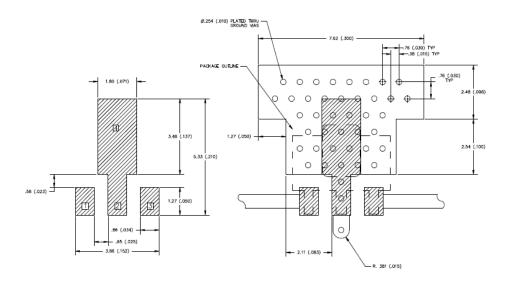
SYMBOL	MIN	NOM	MAX
A - Thickness	1.40	1.50	1.60
C - Lead thickness	0.35		0.43
D - Body width	4.40		4.60
E1 - Body length	2.30		2.60
E - Total length	3.64		4.25
e - Lead spacing	1.40	1.50	1.60
e1 - Dual lead spacing	2.90	3.00	3.10
b - Outer lead width	0.35		0.48
b1 - Center lead width	0.40		0.56
L - Lead length	0.74		1.20
d1 - Tab lead width	1.40		1.80
Above body	0.35		0.64

DIMENSIONS ARE IN MM



## **Mounting Configuration**

All dimensions are in millimeters (inches). Angles are in degrees.



#### Notes:

- 1. Ground / thermal vias are critical for the proper performance of this device. Vias should use a .35mm (#80 / .0135") diameter drill and have a final plated thru diameter of .25 mm (.010").
- 2. Add as much copper as possible to inner and outer layers near the part to ensure optimal thermal performance.

- 6 of 7 -

Disclaimer: Subject to change without notice

© 2010 TriQuint Semiconductor, Inc.

Connecting the Digital World to the Global Network®

Data Sheet: Rev A 08-30-10

High Gain RF Amplifier, 75 Ω, 50-1200 MHz



## **Product Compliance Information**

#### **ESD Information**



#### Caution! ESD-Sensitive Device

ESD Rating: Class 1B

Value: Passes  $\geq 500 \text{V min.}$ 

Test: Human Body Model (HBM)
Standard: JEDEC Standard JESD22-A114

ESD Rating: Class IV

Value: Passes  $\geq 2000 \text{ V}$ 

Test: Charged Device Model (CDM) Standard: JEDEC Standard JESD22-C101

#### **MSL Rating**

MSL 3 at +260 °C convection reflow The part is rated Moisture Sensitivity Level 3 at 260°C per JEDEC standard IPC/JEDEC J-STD-020.

#### **Solderability**

Compatible with the latest version of J-STD-020, Lead free solder, 260°

This part is compliant with EU 2002/95/EC RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment).

This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A  $(C_{15}H_{12}Br_4O_2)$  Free
- PFOS Free
- SVHC Free

#### **Contact Information**

For the latest specifications, additional product information, worldwide sales and distribution locations, and information about TriQuint:

Web: <u>www.triquint.com</u> Tel: +1.707.526.4498 Email: <u>info-sales@tqs.com</u> Fax: +1.707.526.1485

For technical questions and application information:

Email: sjcapplications.engineering@tqs.com

# **Important Notice**

The information contained herein is believed to be reliable. TriQuint makes no warranties regarding the information contained herein. TriQuint assumes no responsibility or liability whatsoever for any of the information contained herein. TriQuint assumes no responsibility or liability whatsoever for the use of the information contained herein. The information contained herein is provided "AS IS, WHERE IS" and with all faults, and the entire risk associated with such information is entirely with the user. All information contained herein is subject to change without notice. Customers should obtain and verify the latest relevant information before placing orders for TriQuint products. The information contained herein or any use of such information does not grant, explicitly or implicitly, to any party any patent rights, licenses, or any other intellectual property rights, whether with regard to such information itself or anything described by such information.

TriQuint products are not warranted or authorized for use as critical components in medical, life-saving, or life-sustaining applications, or other applications where a failure would reasonably be expected to cause severe personal injury or death.

Data Sheet: Rev A 08-30-10 © 2010 TriQuint Semiconductor, Inc.

- 7 of 7 - Disclaimer: Subject to change without notice

Connecting the Digital World to the Global Network®